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#### PNP SURFACE MOUNT TRANSISTO

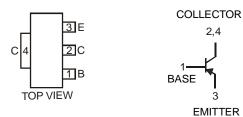
### **Features**

- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DZTA42)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.115 grams (approximate)





Schematic and Pin Configuration

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-300	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Base Current	I <sub>B</sub>	-100	mA
Continuous Collector Current	I <sub>C</sub>	-500	mA

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation @ T <sub>A</sub> = 25°C (Note 3)	$P_d$	1	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = 25°C (Note 3)	$R_{ hetaJA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)	-					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-300		_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-300	_	_	V	$I_C = -1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5		_	V	$I_E = -100 \mu A, I_C = 0$
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_		-0.25	μΑ	V <sub>CB</sub> = -200V, I <sub>E</sub> = 0
Emitter-Base Cut-Off Current	I <sub>EBO</sub>	_		-0.1	μА	$V_{EB} = -3V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_		-0.5	V	$I_C = -20mA$ , $I_B = -2mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_		-0.9	V	$I_C = -20mA$ , $I_B = -2mA$
		25		_		$I_C = -1 \text{mA}, V_{CE} = -10 \text{V}$
DC Current Gain	h <sub>FE</sub>	40	_	_	V	$I_C = -10 \text{mA}, V_{CE} = -10 \text{V}$
		25		_		$I_C = -30 \text{mA}, V_{CE} = -10 \text{V}$
SMALL SIGNAL CHARACTERISTICS						
Gain-Bandwidth Product	f <sub>T</sub>	50		_	MHz	$I_C = -10 \text{mA}, V_{CE} = -20 \text{V}, f = 100 \text{MHz}$
Output Capacitance	$C_{ m obo}$	_	_	6	pF	$V_{CB} = -20V$ , $f = 1MHz$

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Device mounted on FR-4 PCB, 1" x 0.85" x 0.052"; pad layout as shown on page 4 or on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- Measured under pulsed conditions. Pulse Test: Pulse width, tp<300 uS, Duty Cycle, d< = 2%



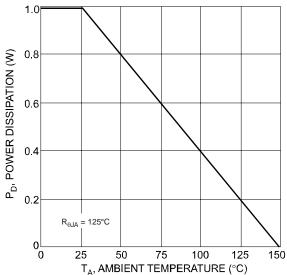


Fig. 1, Power Dissipation vs. Ambient Temperature (Note 3)

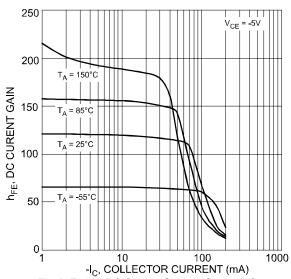


Fig. 3, Typical DC Current Gain vs. Collector Current

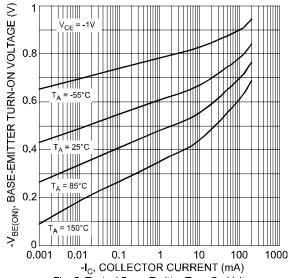
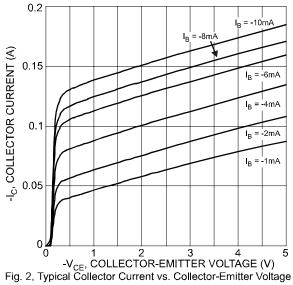


Fig. 5, Typical Base-Emitter Turn-On Voltage vs. Collector Current



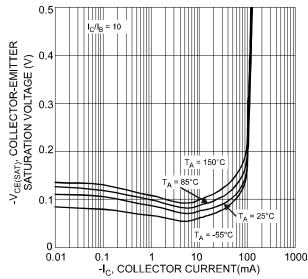


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

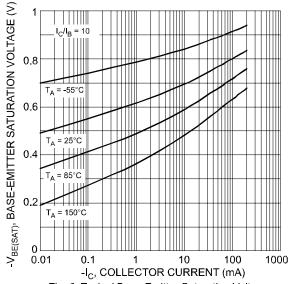
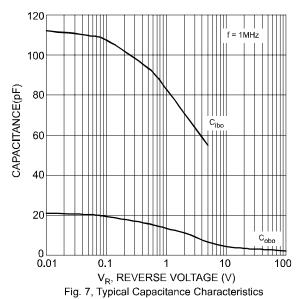


Fig. 6, Typical Base-Emitter Saturation Voltage vs. Collector Current





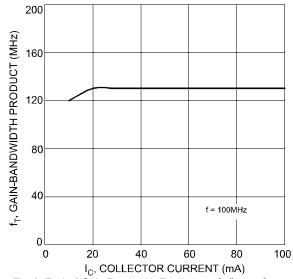


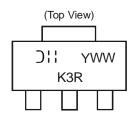
Fig. 8, Typical Gain-Bandwidth Product vs. Collector Current

# **Ordering Information** (Note 5)

Device	Packaging	Shipping
DZTA92-13	SOT-223	2500/Tape & Reel

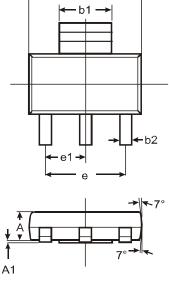
Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

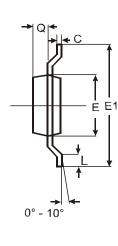
# **Marking Information**



K3R = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

# Package Outline Dimensions

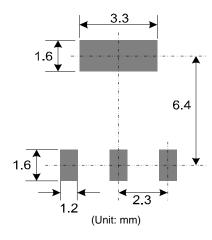




SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
<b>A</b> 1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
e		1	4.60		
e1		1	2.30		
L	0.55	0.75	0.65		
Q	0.84	0.94	0.89		
All Dimensions in mm					



## Suggested Pad Layout: (Based on IPC-SM-782)



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